

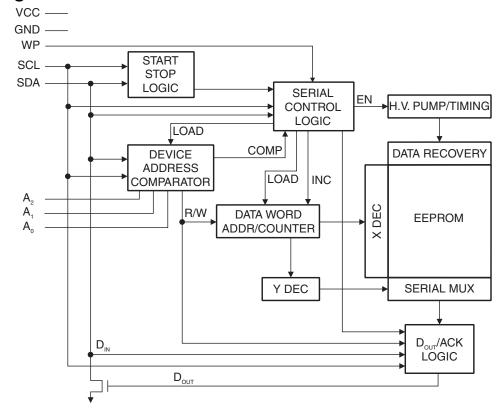
Absolute Maximum Ratings*

Operating Temperature55 to +125°C
Storage Temperature65 to +150°C
Voltage on Any Pin with Respect to Ground1.0 to +7.0V
Maximum Operating Voltage
DC Output Current5.0 mA

*NOTICE:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

1. Block Diagram



2. Pin Description

SERIAL CLOCK (SCL): The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

SERIAL DATA (SDA): The SDA pin is bidirectional for serial data transfer. This pin is open-drain driven and may be wire-ORed with any number of other open-drain or open collector devices.

DEVICE/ADDRESSES (A2, A1, A0): The A2, A1 and A0 pins are device address inputs that are hard wired or left not connected for hardware compatibility with other AT24CXX devices. When the pins are hardwired, as many as eight 32K/64K devices may be addressed on a single bus system (device addressing is discussed in detail under the Device Addressing section). If the pins are left floating, the A2, A1 and A0 pins will be internally pulled down to GND if the capacitive coupling to the circuit board V_{CC} plane is <3pF. If coupling is >3pF, Atmel® recommends connecting the address pins to GND.

WRITE PROTECT (WP): The write protect input, when connected to GND, allows normal write operations. When WP is connected high to V_{CC} , all write operations to the memory are inhibited. If the pin is left floating, the WP pin will be internally pulled down to GND if the capacitive coupling to the circuit board V_{CC} plane is <3pF. If coupling is >3pF, Atmel recommends connecting the pin to GND.





3. Memory Organization

AT24C32C/64C, **32/64K SERIAL EEPROM**: The 32K/64K is internally organized as 128/256 pages of 32 bytes each. Random word addressing requires a 12/13 bit data word address.

Pin Capacitance(1)

Applicable over recommended operating range from T_A = 25°C, f = 1.0 MHz, V_{CC} = +1.8V to 5.5V

Symbol	Test Condition	Max	Units	Conditions
C _{I/O}	Input/Output Capacitance (SDA)	8	pF	$V_{I/O} = 0V$
C _{IN}	Input Capacitance (A ₀ , A ₁ , A ₂ , SCL)	6	pF	$V_{IN} = 0V$

Note: 1. This parameter is characterized and is not 100% tested.

DC Characteristics

Applicable over recommended operating range from: $T_{AI} = -40$ to $+85^{\circ}C$, $V_{CC} = +1.8$ to +5.5V (unless otherwise noted)

Symbol	Parameter	Test Condition		Min	Тур	Max	Units
V _{CC1}	Supply Voltage			1.8		5.5	V
I _{CC1}	Supply Current	V _{CC} = 5.0V	READ at 400 kHz		0.4	1.0	mA
I _{CC2}	Supply Current	V _{CC} = 5.0V	WRITE at 400 kHz		2.0	3.0	mA
	Standby Current	V _{CC} = 1.8V	V V anV			1.0	μΑ
I _{SB1}	(1.8V option)	V _{CC} = 5.5V	$V_{IN} = V_{CC} \text{ or } V_{SS}$			6.0	μΑ
I _{LI}	Input Leakage Current V _{CC} = 5.0V	$V_{IN} = V_{CC} \text{ or } V_{SS}$	$V_{IN} = V_{CC} \text{ or } V_{SS}$		0.10	3.0	μΑ
I _{LO}	Output Leakage Current V _{CC} = 5.0V	V _{OUT} = V _{CC} or V _{SS}			0.05	3.0	μΑ
V _{IL}	Input Low Level ⁽¹⁾			-0.6		V _{CC} x 0.3	V
V _{IH}	Input High Level ⁽¹⁾			V _{CC} x 0.7		V _{CC} + 0.5	V
V _{OL2}	Output Low Level	V _{CC} = 3.0V	I _{OL} = 2.1 mA			0.4	V
V _{OL1}	Output Low Level	V _{CC} = 1.8V	V _{CC} = 1.8V			0.2	V

Note: 1. V_{IL} min and V_{IH} max are reference only and are not tested.

AC Characteristics

Applicable over recommended operating range from $T_{AI} = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{CC} = +1.8\text{V}$ to +5.5V, CL = 1 TTL Gate and 100 pF (unless otherwise noted)

		1.8	3-volt	5.0-		
Symbol	Parameter	Min	Max	Min	Max	Units
f _{SCL}	Clock Frequency, SCL		400		1000	kHz
t _{LOW}	Clock Pulse Width Low	1.3		0.4		μs
t _{HIGH}	Clock Pulse Width High	0.6		0.4		μs
t _i	Noise Suppression Time ⁽¹⁾		100		50	ns
t _{AA}	Clock Low to Data Out Valid	0.05	0.9	0.05	0.55	μs
Time the bus must be free before a new transmission can start ⁽¹⁾		1.3		0.5		μs
t _{HD.STA}	Start Hold Time	0.6		0.25		μs
t _{SU.STA}	Start Set-up Time	0.6		0.25		μs
t _{HD.DAT}	Data In Hold Time	0		0		μs
t _{SU.DAT}	Data In Set-up Time	100		100		ns
t _R	Inputs Rise Time ⁽¹⁾		0.3		0.3	μs
t _F	Inputs Fall Time ⁽¹⁾		300		100	ns
t _{SU.STO}	Stop Set-up Time	0.6		0.25		μs
t _{DH}	Data Out Hold Time	50		50		ns
t _{WR}	Write Cycle Time		5		5	ms
Endurance ⁽¹⁾	25°C, Page Mode, 3.3V	1,000,000				Write Cycles

Notes: 1. This parameter is ensured by characterization.

2. AC measurement conditions:

 $\rm R_L$ (connects to $\rm V_{CC}$): 1.3 k Ω (2.5V, 5.0V), 10 k Ω (1.8V)

Input pulse voltages: 0.3 V_{CC} to 0.7 V_{CC} Input rise and fall times: \leq 50 ns

Input and output timing reference voltages: 0.5 $\ensuremath{V_{\text{CC}}}$





4. Device Operation

CLOCK and DATA TRANSITIONS: The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods (refer to Data Validity timing diagram). Data changes during SCL high periods will indicate a start or stop condition as defined below.

START CONDITION: A high-to-low transition of SDA with SCL high is a start condition which must precede any other command (refer to Start and Stop Definition timing diagram).

STOP CONDITION: A low-to-high transition of SDA with SCL high is a stop condition. After a read sequence, the stop command will place the EEPROM in a standby power mode (refer to Start and Stop Definition timing diagram).

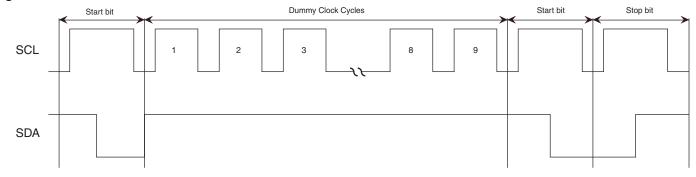
ACKNOWLEDGE: All addresses and data words are serially transmitted to and from the EEPROM in 8-bit words. The EEPROM sends a zero during the ninth clock cycle to acknowledge that it has received each word.

STANDBY MODE: The AT24C32C/64C features a low power standby mode which is enabled: a) upon power-up and b) after the receipt of the Stop bit and the completion of any internal operations.

SOFTWARE RESET: After an interruption in protocol, power loss or system reset, and 2-wire part can be protocol reset by following these steps:

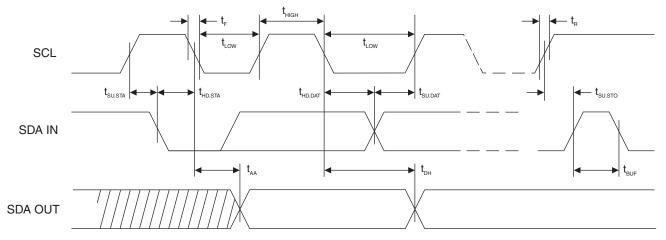
(a) Create a start bit condition, (b) clock 9 cycles, (c) create another start bit followed by stop bit condition as shown below. The device is ready for next communication after above steps have been completed.

Figure 4-1. Software Reset



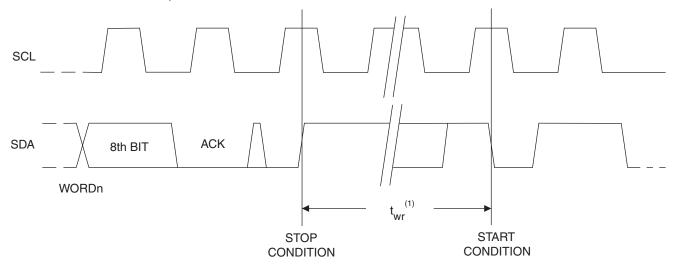
5. Bus Timing

SCL: Serial Clock, SDA: Serial Data I/O



6. Write Cycle Timing

SCL: Serial Clock, SDA: Serial Data I/O

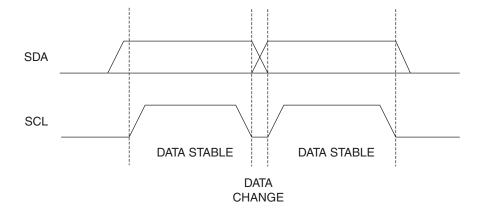


Note: 1. The write cycle time t_{WR} is the time from a valid stop condition of a write sequence to the end of the internal clear/write cycle.

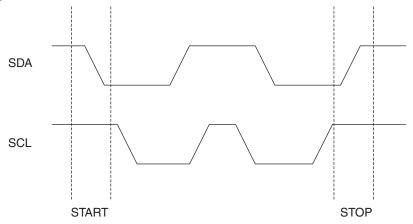




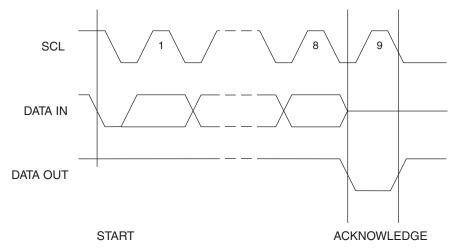
7. Data Validity



8. Start and Stop Definition



9. Output Acknowledge



10. Device Addressing

The 32K/64K EEPROM requires an 8-bit device address word following a start condition to enable the chip for a read or write operation (see Figure 12-1 on page 11). The device address word consists of a mandatory one, zero sequence for the first four most significant bits as shown. This is common to all 2-wire EEPROM devices.

The 32K/64K uses the three device address bits A2, A1, A0 to allow as many as eight devices on the same bus. These bits must compare to their corresponding hardwired input pins. The A2, A1, and A0 pins use an internal proprietary circuit that biases them to a logic low condition if the pins are allowed to float.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a zero. If a compare is not made, the device will return to standby state.

DATA SECURITY: The AT24C32C/64C has a hardware data protection scheme that allows the user to write protect the entire memory when the WP pin is at V_{CC} .

11. Write Operations

BYTE WRITE: A write operation requires two 8-bit data word addresses following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a zero and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a zero and the addressing device, such as a microcontroller, must terminate the write sequence with a stop condition. At this time the EEPROM enters an internally-timed write cycle, t_{WR} , to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete (see Figure 12-2 on page 11).

PAGE WRITE: The 32K/64K EEPROM is capable of 32-byte page writes.

A page write is initiated the same way as a byte write, but the microcontroller does not send a stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to 31 more data words. The EEPROM will respond with a zero after each data word received. The microcontroller must terminate the page write sequence with a stop condition (see Figure 12-3 on page 11).

The data word address lower 5 bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than 32 data words are transmitted to the EEPROM, the data word address will "roll over" and previous data will be overwritten.

ACKNOWLEDGE POLLING: Once the internally-timed write cycle has started and the EEPROM inputs are disabled, acknowledge polling can be initiated. This involves sending a start condition followed by the device address word. The read/write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a zero, allowing the read or write sequence to continue.





12. Read Operations

Read operations are initiated the same way as write operations with the exception that the read/write select bit in the device address word is set to one. There are three read operations: current address read, random address read and sequential read.

CURRENT ADDRESS READ: The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address "roll over" during read is from the last byte of the last memory page, to the first byte of the first page. The address "roll over" during write is from the last byte of the current page to the first byte of the same page.

Once the device address with the read/write select bit set to one is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input zero but does generate a following stop condition (see Figure 12-4 on page 12).

RANDOM READ: A random read requires a "dummy" byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a current address read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a zero but does generate a following stop condition (see Figure 12-5 on page 12).

SEQUENTIAL READ: Sequential reads are initiated by either a current address read or a random address read. After the microcontroller receives a data word, it responds with an acknowledge. As long as the EEPROM receives an acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will "roll over" and the sequential read will continue. The sequential read operation is terminated when the microcontroller does not respond with a zero but does generate a following stop condition (see Figure 12-6 on page 12).

Figure 12-1. Device Address

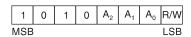


Figure 12-2. Byte Write

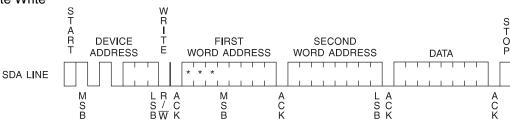
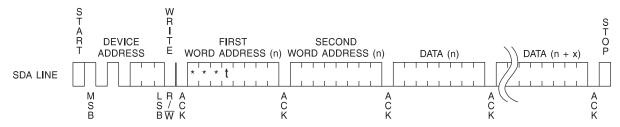


Figure 12-3. Page Write



Note: 1. * = DON'T CARE bits

2. t = DON'T CARE bit for AT24C32C

Figure 12-4. Current Address Read

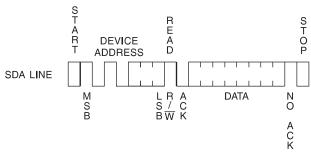
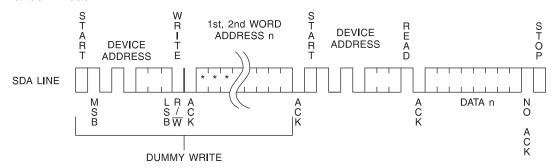


Figure 12-5. Random Read

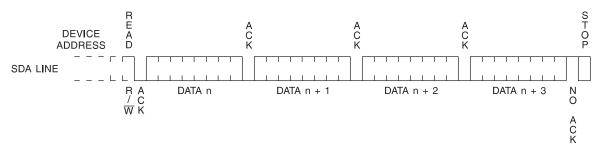


Note: 1. * = DON'T CARE bits





Figure 12-6. Sequential Read



AT24C32C Ordering Information

Ordering Code	Voltage	Package	Operation Range
AT24C32C-PU (Bulk form only)	1.8	8P3	
AT24C32CN-SH-B ⁽¹⁾ (NiPdAu Lead Finish)	1.8	8S1	
AT24C32CN-SH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8S1	Lead-free/Halogen-free
AT24C32C-TH-B ⁽¹⁾ (NiPdAu Lead Finish)	1.8	8A2	Industrial Temperature
AT24C32C-TH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8A2	(-40°C to 85°C)
AT24C32CY6-YH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8Y6	
AT24C32CD3-DH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8D3	
AT24C32CU2-UU-T ⁽²⁾	1.8	8U2-1	
AT24C32C-W-11 ⁽³⁾	1.8	Die Sale	Industrial Temperature (-40°C to 85°C)

Notes:

- 1. "-B" denotes Bulk.
- 2. "-T" denotes tape and reel. SOIC = 4K per reel. TSSOP, Ultra Thin Mini-MAP and dBGA2 = 5K per reel.
- 3. Available in waffle pack, tape and reel, and wafer form; order as SL788 for inkless wafer form. Bumped die available upon request. Please contact Serial Interface Marketing.

Package Type							
8Y6 8-lead, 2.00mm x 3.00mm Body, 0.50mm Pitch, Ultra Thin Mini-MAP, Dual no Lead Package (DFN), (MLP 2							
8P3	8P3 8-lead, 0.300" Wide, Plastic Dual Inline Package (PDIP)						
8S1 8-lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC)							
8A2	8-lead, 4.4 mm Body, Plastic, Thin Shrink Small Outline Package (TSSOP)						
8U2-1	8-ball, die Ball Grid Array Package (dBGA2)						
8D3	8-lead, 1.80 mm x 2.20 mm Body, Ultra Lead Frame Land Grid Array (ULA)						
Options							
-1.8	Low Voltage (1.8V to 5.5V)						





AT24C64C Ordering Information

Ordering Code	Voltage	Package	Operation Range
AT24C64C-PU (Bulk form only)	1.8	8P3	
AT24C64CN-SH-B ⁽¹⁾ (NiPdAu Lead Finish)	1.8	8S1	
AT24C64CN-SH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8S1	Lead-free/Halogen-free
AT24C64C-TH-B ⁽¹⁾ (NiPdAu Lead Finish)	1.8	8A2	Industrial Temperature
AT24C64C-TH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8A2	(-40°C to 85°C)
AT24C64CY6-YH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8Y6	
AT24C64CD3-DH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8D3	
AT24C64CU2-UU-T ⁽²⁾	1.8	8U2-1	
AT24C64C-W-11 ⁽³⁾	1.8	Die Sale	Industrial Temperature (-40°C to 85°C)

Notes:

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- 3. Available in waffle pack, tape and reel, and wafer form; order as SL788 for inkless wafer form. Bumped die available upon request. Please contact Serial Interface Marketing.

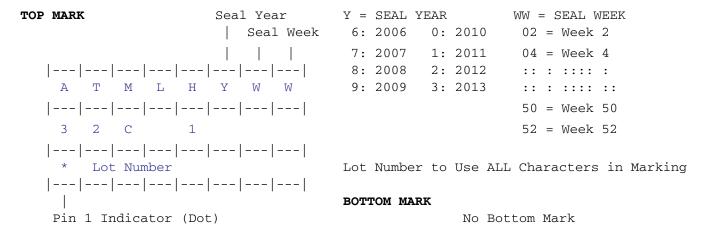
Package Type						
8Y6 8-lead, 2.00mm x 3.00mm Body, 0.50mm Pitch, Ultra Thin Mini-MAP, Dual no Lead Package (DFN), (MLP 2						
8P3 8-lead, 0.300" Wide, Plastic Dual Inline Package (PDIP)						
8S1 8-lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC)						
8A2 8-lead, 4.4 mm Body, Plastic, Thin Shrink Small Outline Package (TSSOP)						
8U2-1	8-ball, die Ball Grid Array Package (dBGA2)					
8D3	8-lead, 1.80 mm x 2.20 mm Body, Ultra Lead Frame Land Grid Array (ULA)					
Options						
-1.8 Low Voltage (1.8V to 5.5V)						

13. Part Marking Scheme

13.1 8-PDIP

TOP MARK	Seal Year	Y =	SEAL	YEAR		WW = SEAL WEEK
	Seal Week	6:	2006	0:	2010	02 = Week 2
	1 1 1	7:	2007	1:	2011	04 = Week 4
	-	8:	2008	2:	2012	:: : :::: :
A T M L U	Y W W	9:	2009	3:	2013	:: : :::: ::
	-					50 = Week 50
3 2 C 1						52 = Week 52
	-					
* Lot Number		Lot	Numbe	er to	Use ALL	Characters in Marking
	-					
1		BOT	TOM MA	ARK		
Pin 1 Indicator (D	ot)				No Bot	tom Mark

13.2 8-SOIC







13.3 8-TSSOP

TOP MARK

Pir	n 1 :	Indio	cato	r (Do	t)
*	Н	Y	M	M	
3	2	С		1	

Y =	SEAL	YEAR		WW	=	= 5	SEAL	WEEK
6:	2006	0:	2010	0	2	=	Week	2
7:	2007	1:	2011	0	4	=	Week	4
8:	2008	2:	2012	:	:	:	::::	:
9:	2009	3:	2013	:	:	:	::::	::
				5	0	=	Week	50
				5	2	=	Week	52

BOTTOM MARK

13.4 8-Ultra Thin Mini MAP

TOP MARK

Y = YEAR OF ASSEMBLY

XX = ATMEL LOT NUMBER TO COORESPOND WITH
NSEB TRACE CODE LOG BOOK.
(e.g. XX = AA, AB, AC,...AX, AY, AZ)

Y = SEAL YEAR
6: 2006 0: 2010
7: 2007 1: 2011
8: 2008 2: 2012
9: 2009 3: 2013

13.5 8-ULA

TOP MARK

$$Y = YEAR OF ASSEMBLY$$

XX = ATMEL LOT NUMBER TO COORESPOND WITH NSEB TRACE CODE LOG BOOK. (e.g. XX = AA, AB, AC,...AX, AY, AZ)

Y = BUILD YEAR 6: 2006 7: 2007 8: 2008

Etc...



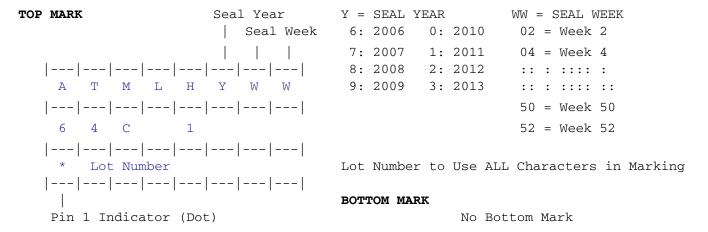


14. Part Marking Scheme

14.1 8-PDIP

TOP	MARK	Seal Year	Y =	SEAL	YEAR		WW = SEAL WEEK
		Seal Week	6 :	2006	0:	2010	02 = Week 2
		1 1	7:	2007	1:	2011	04 = Week 4
			8:	2008	2:	2012	:: : :::: :
	A T M L U	Y W W	9:	2009	3:	2013	:: : :::: ::
							50 = Week 50
	6 4 C 1						52 = Week 52
	* Lot Number		Lot	Numbe	r to	Use ALL	Characters in Marking
			BOTI	OM MA	RK		
	Pin 1 Indicator (Do	t)				No Bott	com Mark

14.2 8-SOIC



14.3 8-TSSOP

TOP MARK

Pir	n 1 :	Indic	cator	r (Dot)
- 1					
*	Н	Y	W	M	
6	4	С		1	

Y =	SEAL	YEAR		WW	= ;	SEAL	WEEK
6:	2006	0:	2010	02	2 =	Week	2
7:	2007	1:	2011	0 4	1 =	Week	4
8:	2008	2:	2012	::	:	::::	:
9:	2009	3:	2013	::	:	::::	::
				50) =	Week	50
				52	2 =	Week	52

BOTTOM MARK

14.4 8-Ultra Thin Mini MAP

TOP MARK

Y = YEAR OF ASSEMBLY

XX = ATMEL LOT NUMBER TO COORESPOND WITH
NSEB TRACE CODE LOG BOOK.
(e.g. XX = AA, AB, AC,...AX, AY, AZ)

Y = SEAL YEAR
6: 2006 0: 2010
7: 2007 1: 2011
8: 2008 2: 2012
9: 2009 3: 2013





14.5 8-ULA

TOP MARK

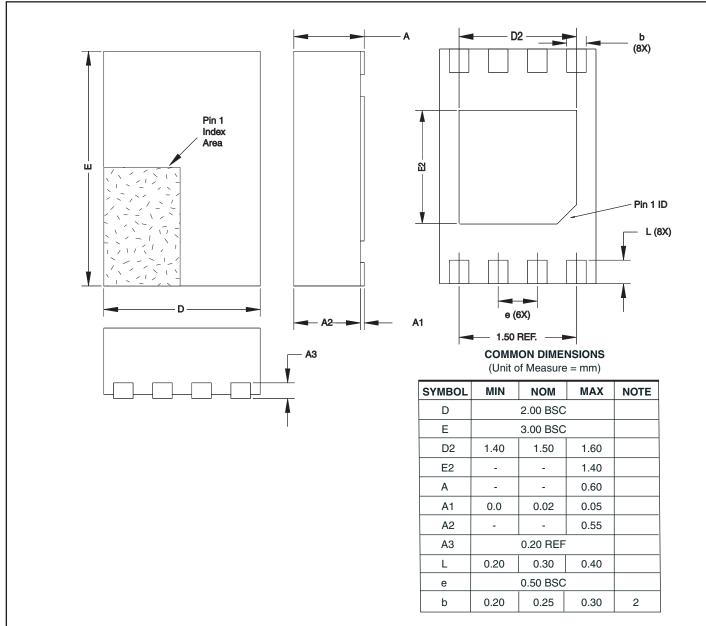
Y = YEAR OF ASSEMBLY

XX = ATMEL LOT NUMBER TO COORESPOND WITH NSEB TRACE CODE LOG BOOK. (e.g. XX = AA, AB, AC,...AX, AY, AZ)

Y = BUILD YEAR 6: 2006 7: 2007 8: 2008 Etc...

15. Packaging Information

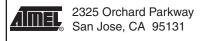
8Y6 - MLP



Notes:

- 1. This drawing is for general information only. Refer to JEDEC Drawing MO-229, for proper dimensions, tolerances, datums, etc.
- 2. Dimension b applies to metallized terminal and is measured between 0.15 mm and 0.30 mm from the terminal tip. If the terminal has the optional radius on the other end of the terminal, the dimension should not be measured in that radius area.
- 3. Soldering the large thermal pad is optional, but not recommended. No electrical connection is accomplished to the device through this pad, so if soldered it should be tied to ground

10/16/07



TITLE 8Y6, 8-lead 2.0 x 3.0 mm Body, 0.50 mm Pitch, Utlra Thin Mini-Map,

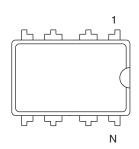
Dual No Lead Package (DFN), (MLP 2x3)

DRAWING NO. REV. 8Y6 D

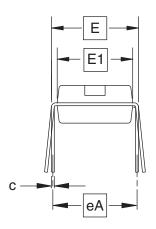




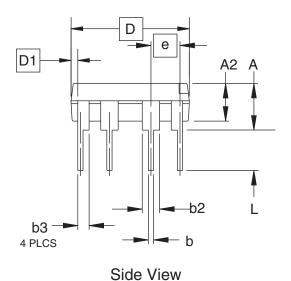
8P3 - PDIP



Top View



End View



COMMON DIMENSIONS

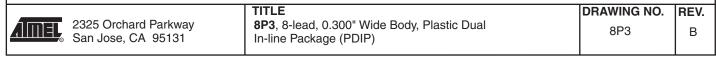
(Unit of Measure = inches)

SYMBOL	MIN	NOM	MAX	NOTE
Α			0.210	2
A2	0.115	0.130	0.195	
b	0.014	0.018	0.022	5
b2	0.045	0.060	0.070	6
b3	0.030	0.039	0.045	6
С	0.008	0.010	0.014	
D	0.355	0.365	0.400	3
D1	0.005			3
Е	0.300	0.310	0.325	4
E1	0.240	0.250	0.280	3
е	0.100 BSC			
eA	0.300 BSC			4
L	0.115	0.130	0.150	2

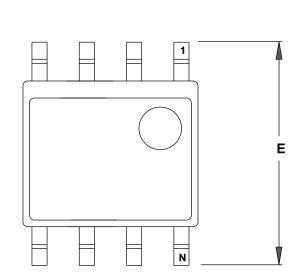
Notes:

- 1. This drawing is for general information only; refer to JEDEC Drawing MS-001, Variation BA for additional information.
- 2. Dimensions A and L are measured with the package seated in JEDEC seating plane Gauge GS-3.
- 3. D, D1 and E1 dimensions do not include mold Flash or protrusions. Mold Flash or protrusions shall not exceed 0.010 inch.
- 4. E and eA measured with the leads constrained to be perpendicular to datum.
- 5. Pointed or rounded lead tips are preferred to ease insertion.6. b2 and b3 maximum dimensions do not include Dambar protrusions. Dambar protrusions shall not exceed 0.010 (0.25 mm).

01/09/02

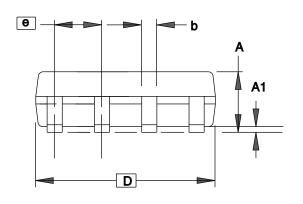


8S1 - JEDEC SOIC



TOP VIEW

SIDE VIEW



C E1

END VIEW

COMMON DIMENSIONS (Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
Α	1.35	_	1.75	
A1	0.10	-	0.25	
b	0.31	-	0.51	
С	0.17	-	0.25	
D	4.80	_	5.05	
E1	3.81	-	3.99	
Е	5.79	_	6.20	
е	1.27 BSC			
L	0.40	_	1.27	
θ	0°	_	8°	

Note: These drawings are for general information only. Refer to JEDEC Drawing MS-012, Variation AA for proper dimensions, tolerances, datums, etc.

3/17/05

<u>AMEL</u>

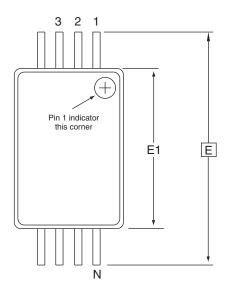
1150 E. Cheyenne Mtn. Blvd. Colorado Springs, CO 80906 **TITLE 8S1**, 8-lead (0.150 Wide Body), Plastic Gull Wing Small Outline (JEDEC SOIC)

BS1 REV.

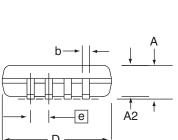




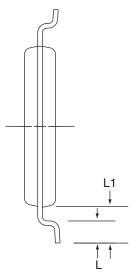
8A2 - TSSOP



Top View



Side View



End View

COMMON DIMENSIONS

(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
D	2.90	3.00	3.10	2, 5
Е		6.40 BSC		
E1	4.30	4.40	4.50	3, 5
Α	_	_	1.20	
A2	0.80	1.00	1.05	
b	0.19	-	0.30	4
е		0.65 BSC		
L	0.45	0.60	0.75	
L1		1.00 REF		

Notes: 1. This drawing is for general information only. Refer to JEDEC Drawing MO-153, Variation AA, for proper dimensions, tolerances, datums, etc.

- 2. Dimension D does not include mold Flash, protrusions or gate burrs. Mold Flash, protrusions and gate burrs shall not exceed 0.15 mm (0.006 in) per side.
- 3. Dimension E1 does not include inter-lead Flash or protrusions. Inter-lead Flash and protrusions shall not exceed 0.25 mm (0.010 in) per side.
- 4. Dimension b does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the b dimension at maximum material condition. Dambar cannot be located on the lower radius of the foot. Minimum space between protrusion and ad acent lead is 0.07 mm.
- 5. Dimension D and E1 to be determined at Datum Plane H.

5/30/02

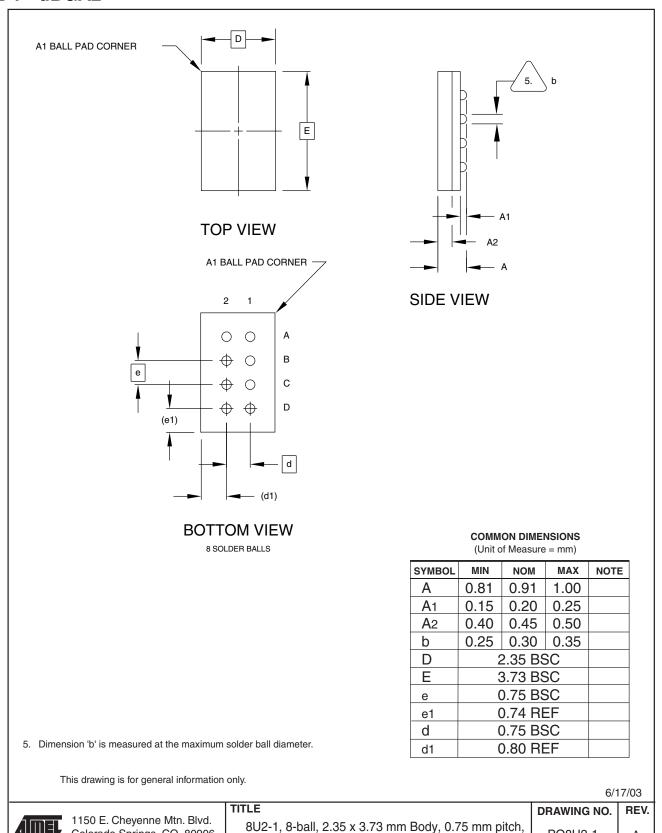


2325 Orchard Parkway San Jose, CA 95131

DRAWING NO.	REV.
8A2	В

24

8U2-1 - dBGA2





Small Die Ball Grid Array Package (dBGA2)

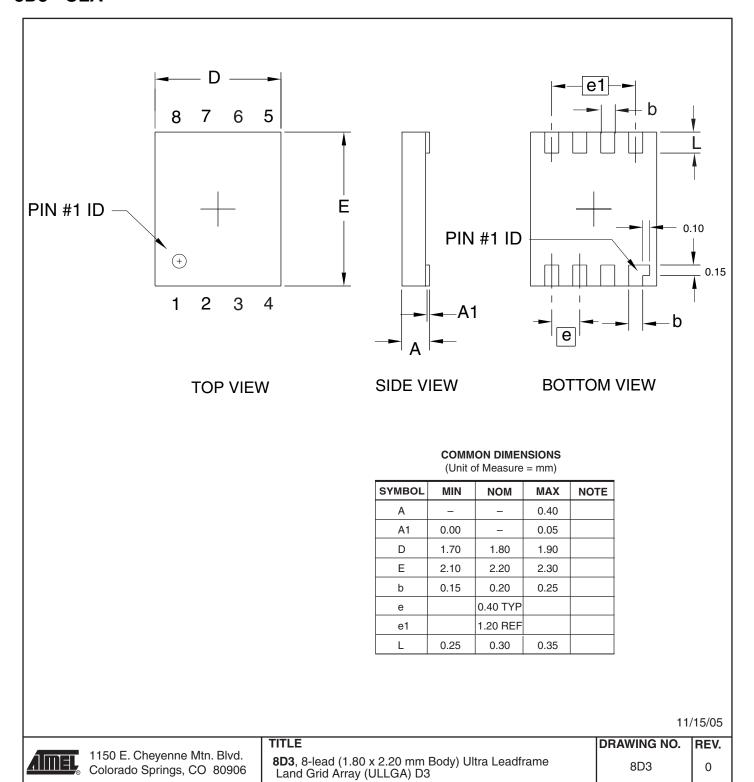
Α

PO8U2-1

Colorado Springs, CO 80906



8D3 - ULA



Revision History

Doc. Rev.	Date	Comments
5298A	1/2008	AT24C32C/64C product with date code 2008 work week 14 (814) or later supports 5Vcc operation Initial document release





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